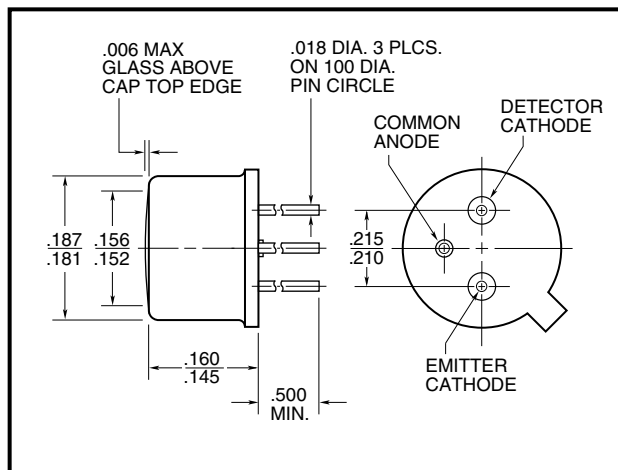


**FEATURES**

- Monitoring diode for power output stability
- Monolithic construction
- Low unit price compared to adding a separate photodiode

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified. Window caps are welded to the case.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_O	$I_F = 100\text{mA}$	18	20		mW
Peak Emission Wavelength, λ_p	$I_F = 50\text{mA}$		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Half Intensity Beam Angle, θ			80		Deg
Forward Voltage, V_F	$I_F = 100\text{mA}$		1.55	1.9	Volts
Reverse Breakdown Voltage, V_R	$I_R = 10\mu\text{A}$	5	30		Volts
Capacitance, C	$V_R = 0\text{V}$		17		pF
Emitter Response Time			0.5		μsec
Monitoring Detector Response Time			1		μsec
Monitoring Detector Output	$F = 100\text{mA}$		50		μA

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation	190mW
Continuous Forward Current	100mA
Peak Forward Current (10 μs , 400Hz)	3A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	240°C

THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C TO 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R (Ambient Temperature)	400°C/W Typical
Thermal Resistance, R (Infinite Heta Sink)	135°C/W Typical

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